

## In the Claims

Claims 1-46 (canceled)

47. (currently amended) A cellular telephone apparatus comprising:

a transceiver;

an antenna; and

an RF power amplifier coupled between the transceiver and the antenna, the RF power amplifier further comprises:

a first switching device having first and second terminals;

a second switching device having first and second terminals, wherein a voltage

differential is applied between the first terminal of the first switching device and

the second terminal of the second switching device, and wherein the first and

second switching devices are implemented using a complementary metal oxide

semiconductor (CMOS); and

an inductance coupled between the second terminal of the first switching device and the

second terminal of the second switching device;

48. (previously presented) The cellular telephone apparatus of claim 47, wherein the first and second switching devices are driven by signals that repeatedly turn the devices on and off.

49. (previously presented) The cellular telephone apparatus of claim 48, wherein the first and second switching devices are both cycled on during the same time period, and wherein the first and second switching devices are both cycled off during the same time period.

Claim 50 (canceled)

51. (currently amended) An RF apparatus used for wireless communications comprising:  
a transceiver for transmitting and receiving signals;  
an RF power amplifier coupled to the transceiver, the RF power amplifier having first and second transistors coupled between a voltage differential, an inductor coupled between the first and second transistors, wherein the first and second transistors are driven by repeatedly turning both transistors on and off, and wherein the first and second transistors are implemented using a complementary metal oxide semiconductor (CMOS); and  
an antenna coupled to the RF power amplifier and the transceiver for transmitting and receiving signals.

52. (previously presented) The RF apparatus of claim 51, wherein the RF power amplifier further comprises third and fourth transistors coupled between a voltage differential, wherein there is an inductance between the third and fourth transistors.

53. (previously presented) The RF apparatus of claim 52, wherein the third and fourth transistors are driven by repeatedly turning the third and fourth transistors on and off.

54. (previously presented) The RF apparatus of claim 52, wherein the RF power amplifier is configured such that the first and second transistors are both turned on and the third and fourth transistors are both turned off during a first time period.

55. (previously presented) The RF apparatus of claim 54, wherein the RF power amplifier is configured such that the first and second transistors are both turned off and the third and fourth transistors are both turned on during a second time period.

Claim 56 (canceled)

57. (previously presented) A cellular telephone apparatus comprising:  
a transceiver for transmitting and receiving signals;  
an RF power amplifier coupled to the transceiver, the RF power amplifier being formed on a complementary metal oxide semiconductor (CMOS), the RF power amplifier further comprising first and second transistors coupled between a voltage differential with an inductance formed between the first and second transistors;  
an antenna coupled to the RF power amplifier and the transceiver for transmitting and receiving signals; and  
wherein the RF power amplifier is configured such that during a first time period, the first and second transistors are turned on to apply a voltage the inductance, and during a second time period, the first and second transistors are turned off.

58. (previously presented) The cellular telephone apparatus of claim 57, wherein the RF power amplifier further comprises a third and fourth transistor coupled between a voltage differential, wherein an inductance is formed between the third and fourth transistors.

59. (previously presented) The cellular telephone apparatus of claim 58, wherein during the first time period, the third and fourth transistors are turned off, and during the second time period, the third and fourth transistors are turned on.

60. (previously presented) The cellular telephone apparatus of claim 59, wherein the third and fourth transistors are not turned on during the first time period.

61. (previously presented) The cellular telephone apparatus of claim 59, wherein the first and second transistors are not turned on during the second time period.

62. (previously presented) The cellular telephone apparatus of claim 59, wherein the first and second transistors are driven by repeatedly turning the first and second transistors on and off.

63. (previously presented) The cellular telephone apparatus of claim 62, wherein the third and fourth transistors are driven by repeatedly turning the third and fourth transistors on and off.

64. (previously presented) The cellular telephone apparatus of claim 63, wherein the first and second transistors are driven out of phase with the third and fourth transistors.

65. (previously presented) The cellular telephone apparatus of claim 57, wherein the first transistors is comprised of an n-channel device, and the second transistor is comprised of a p-channel device.

66. (previously presented) The cellular telephone apparatus of claim 57, wherein the first transistors is comprised of a p-channel device, and the second transistor is comprised of an n-channel device.